

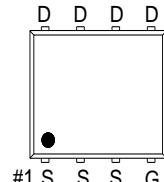
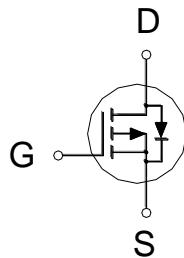
NIKO-SEM**P-Channel Logic Level Enhancement Mode****PE507BA****Field Effect Transistor**

PDFN 3x3P

Halogen-free & Lead-Free

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
-30V	14mΩ	-42A



G : GATE
D : DRAIN
S : SOURCE

**ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)**

PARAMETERS/TEST CONDITIONS	SYMBOL	LIMITS	UNITS
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	±25	V
Continuous Drain Current ³	I_D	-42	A
		-26	
		-12	
		-9.7	
Pulsed Drain Current ¹	I_{DM}	-80	
Avalanche Current	I_{AS}	-42	
Avalanche Energy	E_{AS}	87	mJ
Power Dissipation ⁴	P_D	37	W
		15	
		3.1	
		2	
Junction & Storage Temperature Range	T_j, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE		SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient ²	$t \leq 10\text{s}$	$R_{\theta JA}$	°C/W	40	°C/W
Junction-to-Ambient ²	Steady-State	$R_{\theta JA}$		60	
Junction-to-Case		$R_{\theta JC}$		3.3	

¹Pulse width limited by maximum junction temperature.

²The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

³Package limitation current is 22A

⁴The Power dissipation is based on $R_{\theta JA} t \leq 10\text{s}$ value.

NIKO-SEM**P-Channel Logic Level Enhancement Mode****PE507BA****Field Effect Transistor****PDFN 3x3P****Halogen-free & Lead-Free****ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, Unless Otherwise Noted)**

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = -250\mu\text{A}$	-30			V
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = -250\mu\text{A}$	-1	-1.5	-3	
Gate-Body Leakage	I_{GSS}	$V_{\text{DS}} = 0\text{V}, V_{\text{GS}} = \pm 25\text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}} = -24\text{V}, V_{\text{GS}} = 0\text{V}$			-1	μA
		$V_{\text{DS}} = -20\text{V}, V_{\text{GS}} = 0\text{V}, T_J = 55^\circ\text{C}$			-10	
Drain-Source On-State Resistance ¹	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}} = -4.5\text{V}, I_D = -9\text{A}$		14.5	22	$\text{m}\Omega$
		$V_{\text{GS}} = -10\text{V}, I_D = -10\text{A}$		9.6	14	
Forward Transconductance ¹	g_{fs}	$V_{\text{DS}} = -10\text{V}, I_D = -10\text{A}$		32		S

DYNAMIC

Input Capacitance	C_{iss}	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = -15\text{V}, f = 1\text{MHz}$	2100		pF
Output Capacitance	C_{oss}		365		
Reverse Transfer Capacitance	C_{rss}		327		
Gate Resistance	R_g	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = 0\text{V}, f = 1\text{MHz}$	3		Ω
Total Gate Charge ²	Q_g	$V_{\text{DS}} = -15\text{V}, V_{\text{GS}} = -10\text{V}, I_D = -10\text{A}$	49.1		nC
Gate-Source Charge ²	Q_{gs}		6		
Gate-Drain Charge ²	Q_{gd}		12.3		
Turn-On Delay Time ²	$t_{\text{d}(\text{on})}$	$V_{\text{DD}} = -15\text{V}$ $I_D \approx -10\text{A}, V_{\text{GS}} = -10\text{V}, R_{\text{GEN}} = 6\Omega$	24		nS
Rise Time ²	t_r		24		
Turn-Off Delay Time ²	$t_{\text{d}(\text{off})}$		85		
Fall Time ²	t_f		50		

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_J = 25^\circ\text{C}$)

Continuous Current	I_S			-30	A
Forward Voltage ¹	V_{SD}	$I_F = -10\text{A}, V_{\text{GS}} = 0\text{V}$		-1.2	V
Reverse Recovery Time	t_{rr}	$I_F = -10\text{A}, dI/dt = 100\text{A}/\mu\text{s}$	20.5		nS
Reverse Recovery Charge	Q_{rr}		8.3		uC

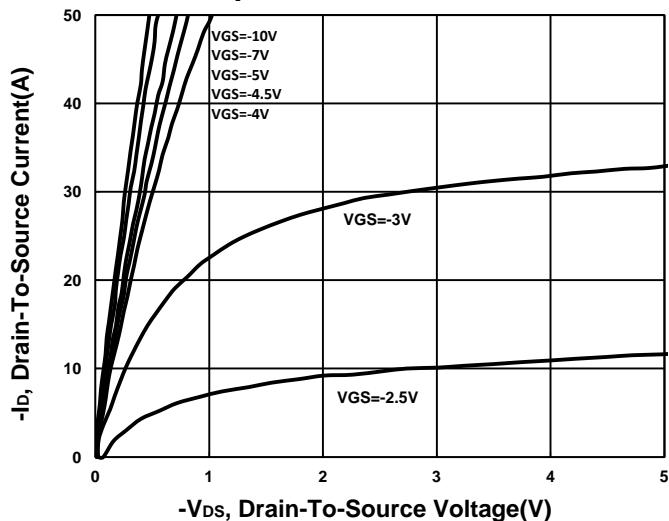
¹Pulse test : Pulse Width $\leq 300\ \mu\text{sec}$, Duty Cycle $\leq 2\%$.²Independent of operating temperature.

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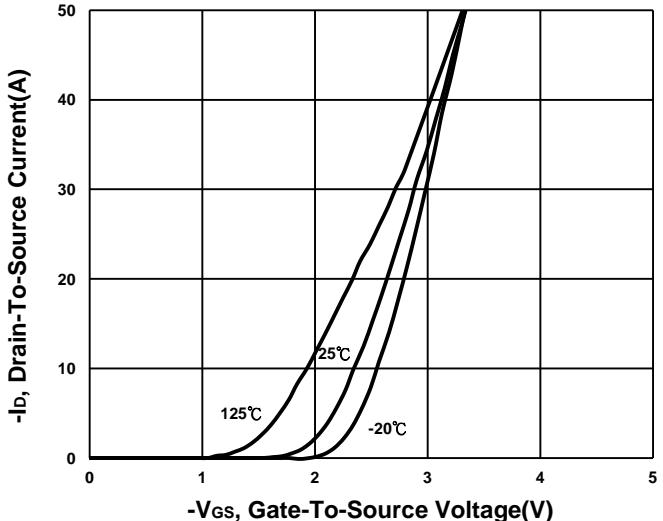
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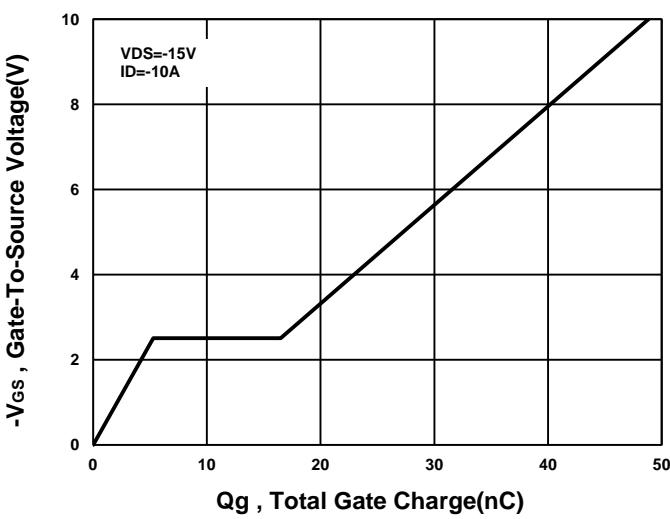
Output Characteristics



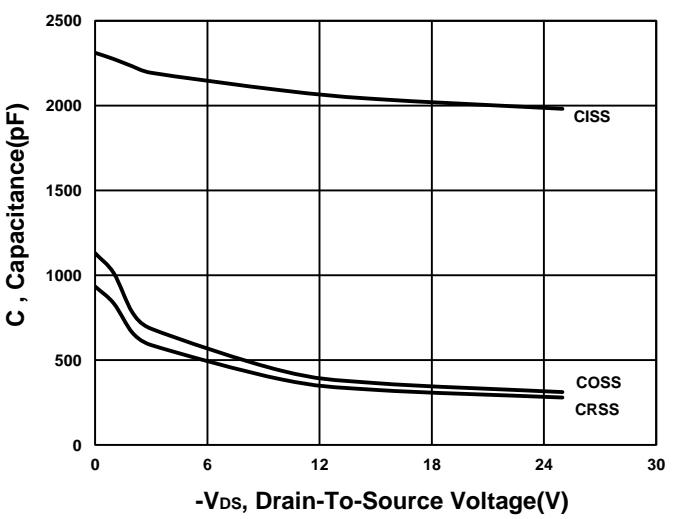
Transfer Characteristics



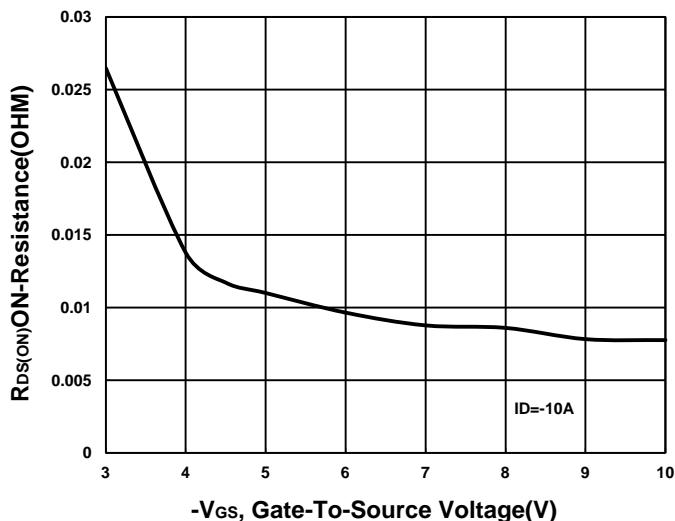
Gate charge Characteristics



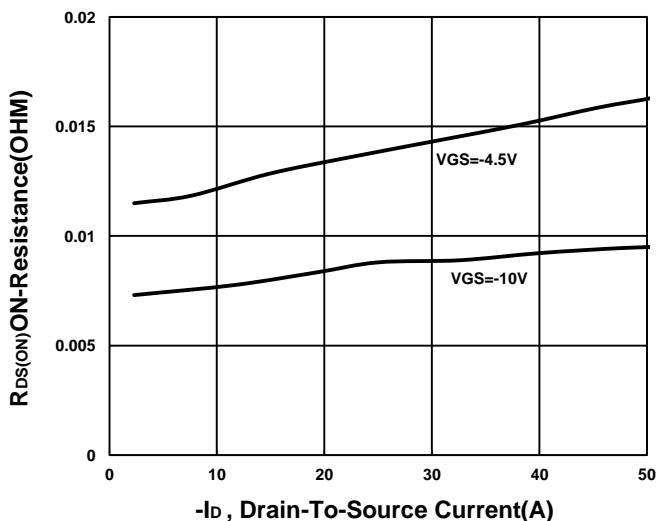
Capacitance Characteristic

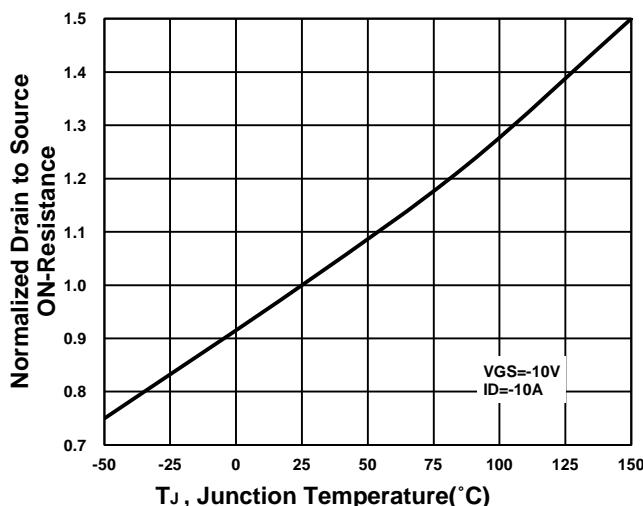
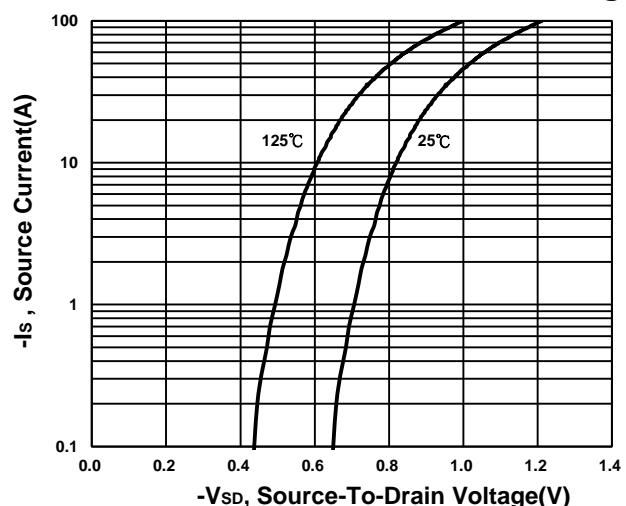
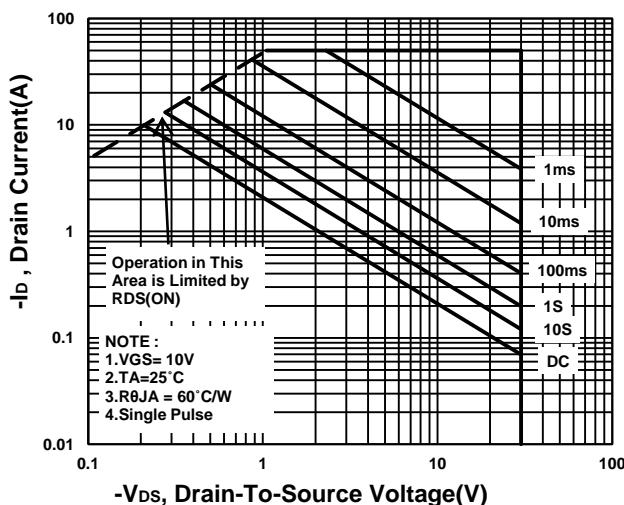
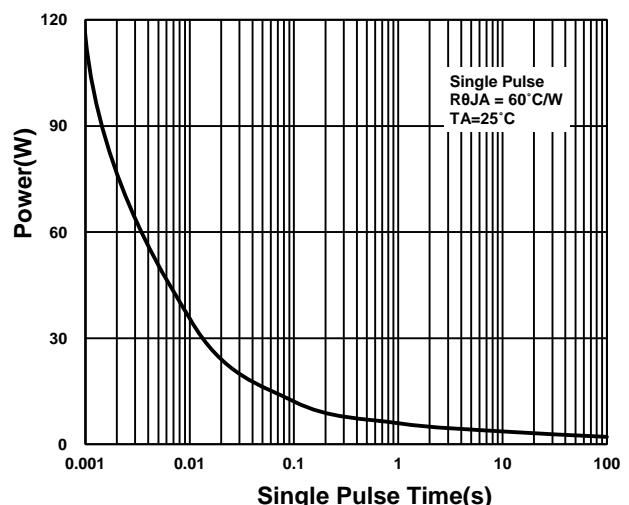
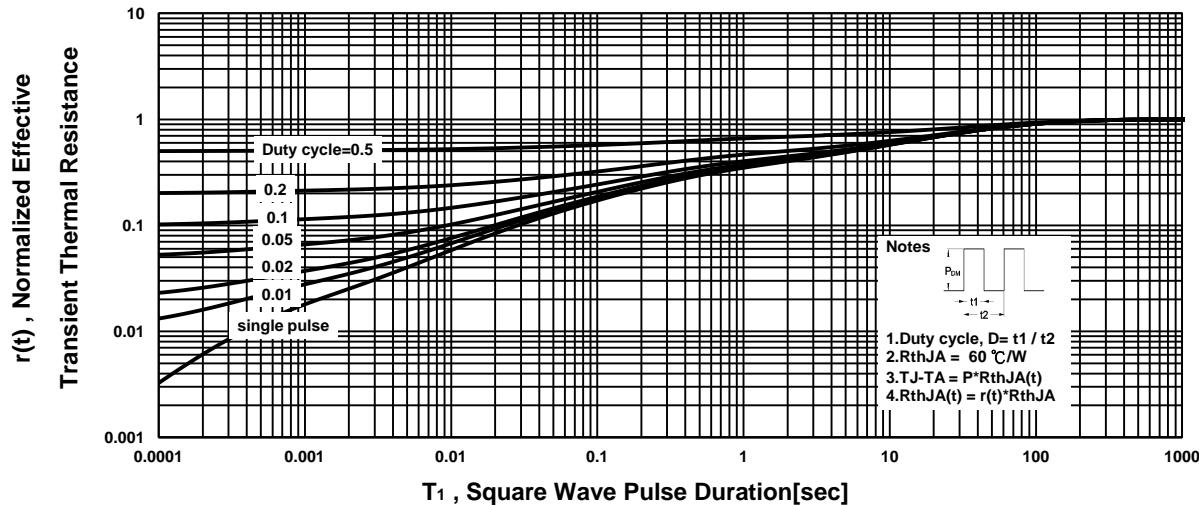


On-Resistance VS Gate-To-Source



On-Resistance VS Drain Current



NIKO-SEM**P-Channel Logic Level Enhancement Mode****PE507BA****Field Effect Transistor****PDFN 3x3P****Halogen-free & Lead-Free****On-Resistance VS Temperature****Source-Drain Diode Forward Voltage****Safe Operating Area****Single Pulse Maximum Power Dissipation****Transient Thermal Response Curve**

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